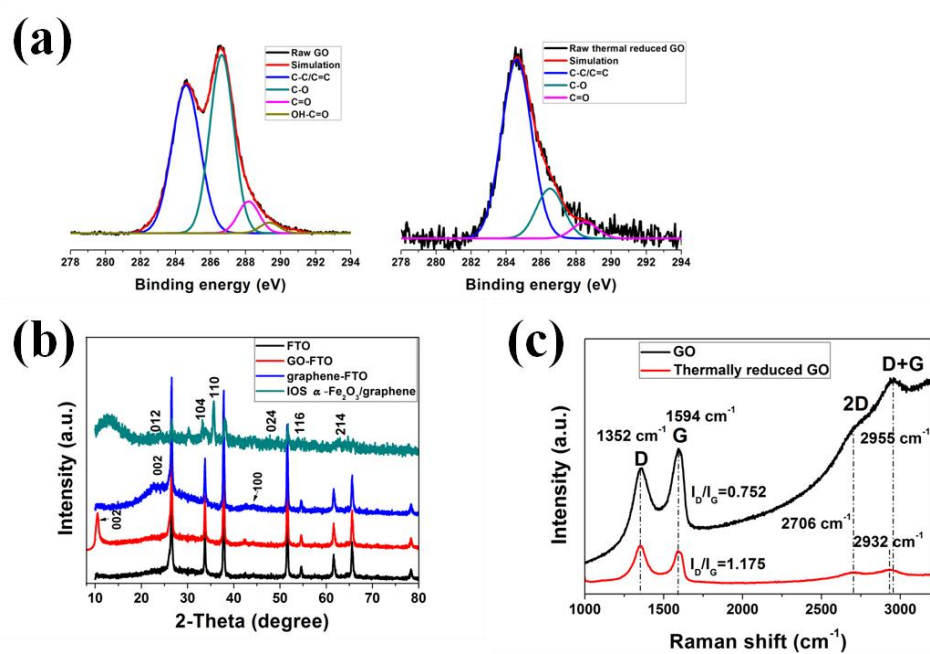


## Supporting Information



**Figure S1.** (a) C1s XPS spectra of GO and graphene film. (b) XRD patterns of GO, graphene and IOS  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>/graphene film,

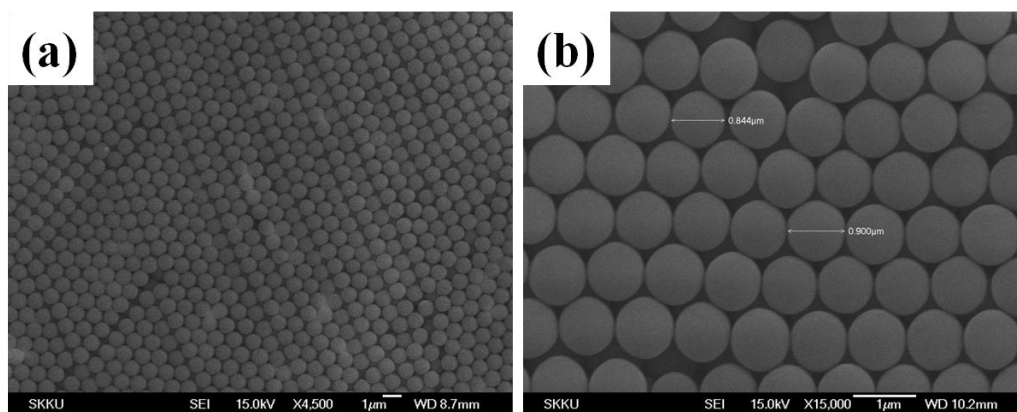
| <b>Samples</b><br><b>Bonds</b> | <b>GO film</b> | <b>Graphene film</b> |
|--------------------------------|----------------|----------------------|
| $A_{C-O}/A_{C-C/C=C}$          | 1.018          | 0.253                |
| $A_{C=O}/A_{C-C/C=C}$          | 0.161          | 0.076                |
| $A_{OH-C=O}/A_{C-C/C=C}$       | 0.019          |                      |

**Table S1.** The peak area (A) ratios of the oxygen-containing bonds to the C-C/C=C bonds for GO and graphene film.

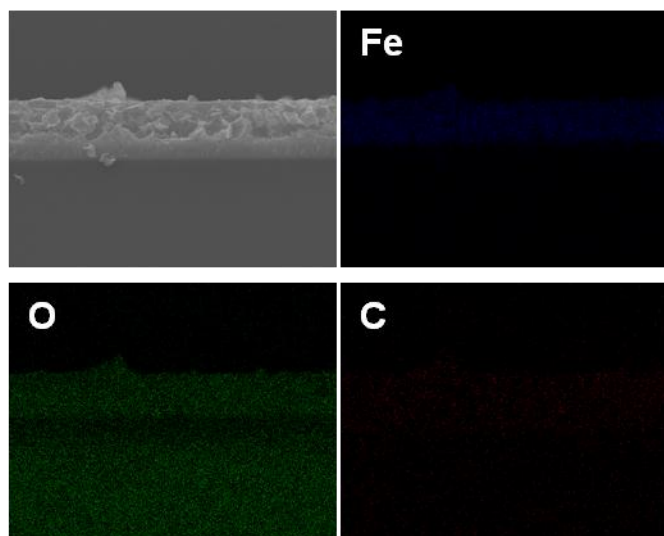
The deconvoluted C1s peaks centered at the binding energies of 286.4, 286.6, 288.1, and 289.3 eV are assigned to the C-C/C=C, C-O, C=O and OH-C=O functional groups on the graphene oxide film surface, respectively [1]. After thermally reducing GO, the concentrations of these functional groups are remarkably decreased, the relative oxygen concentrations are calculated and summarized in Table S1.

The characteristic  $2\theta$  peak of GO film appearing at  $11.07^\circ$  corresponds to a d-spacing of approximately 7.984 Å. the substantial shift of the (002) reflection from 7.98 to 3.6 Å after reduction processing of GO confirms the formation of graphene from GO. These diffraction peaks can be readily indexed to rhombohedral  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>. Almost similar peaks are observed in the XRD pattern of FTO prove this analysis.

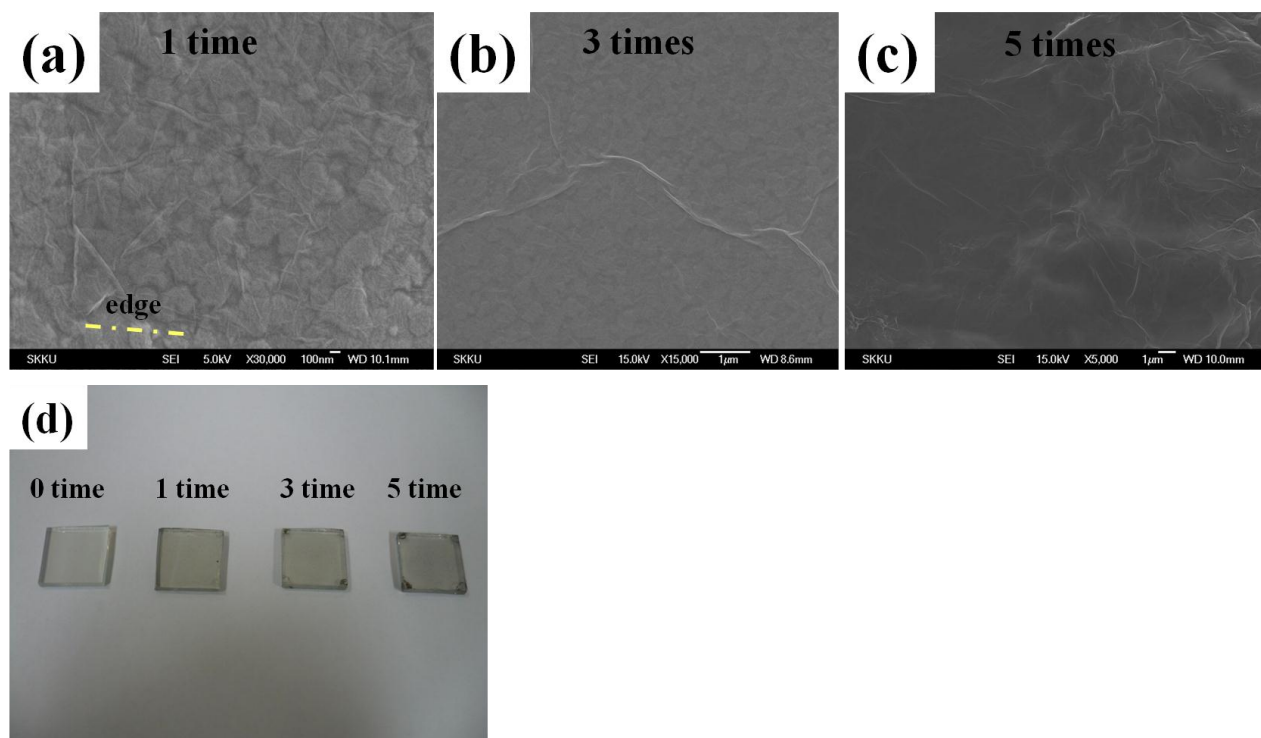
The Raman spectrum of GO film displays two prominent peaks:  $\sim 1352$  and  $\sim 1594$  cm<sup>-1</sup>, which corresponds to the well-documented D and G bands, respectively. The second order Raman feature, the 2D band at  $\sim 2706$  cm<sup>-1</sup> and D+G bands at  $\sim 2955$  cm<sup>-1</sup> is very sensitive to the stacking order of the graphene sheets along the c-axis as well as to the number of layers. G and D bands correspond to the in-plane vibration of sp<sup>2</sup> bonded carbon atoms [2] and the presence of sp<sup>3</sup> defects [3]. The intensity ratio for graphene film (1.175) shows an enhanced value compared to that for GO (0.752), indicating the presence of more localized sp<sup>3</sup> defects within the sp<sup>2</sup> carbon network after thermal reduction.



**Figure S2.** FE-SEM image of PS/graphene colloid templates.

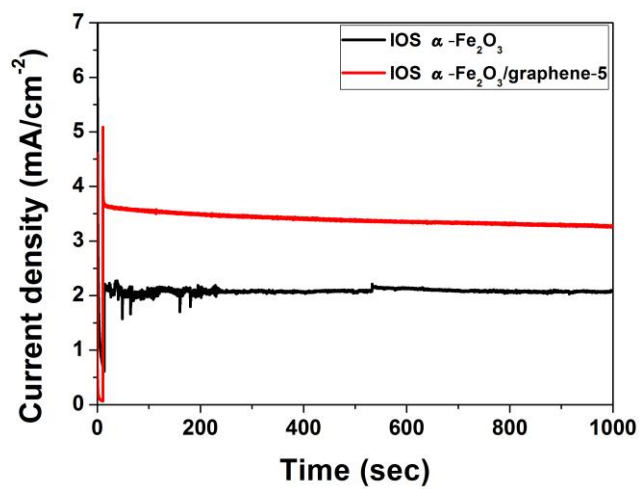


**Figure S3.** EDS elemental maps with Fe, O and C of  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>/graphene/FTO film.



**Figure S4.** FE-SEM images (a-c) and photograph (d) of different layered graphene thin film.

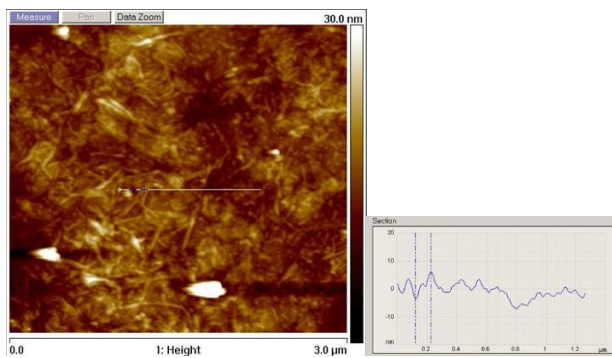
FE-SEM images of different layered graphene film, from Fig. S5, it is clear to see that the FTO substrate gradually become unclear with increasing spin-coating time.



**Figure S5.** Long term of stability for  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub> and  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>/graphene-5 photoanodes under closed circuit conditions at applied potential of 0.5 V.

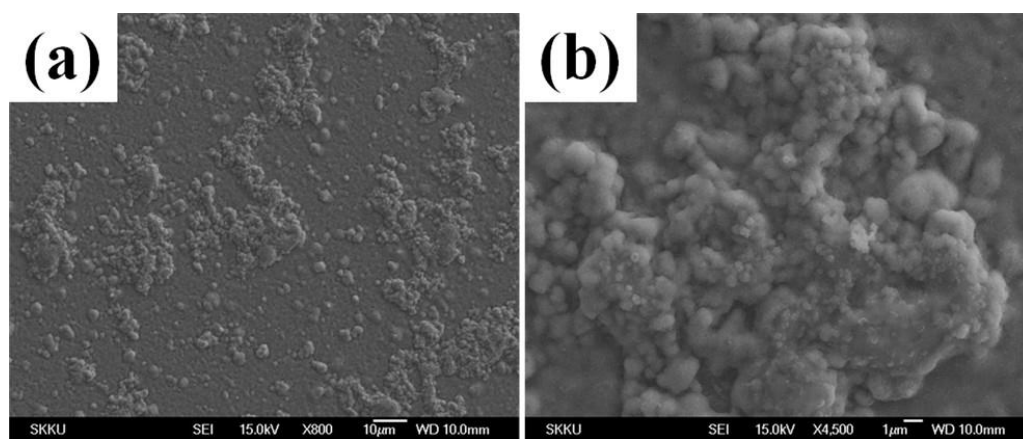
| <b>Graphene coating time</b> | <b>Resistance (M<math>\Omega</math>)</b> |
|------------------------------|--|
| <b>1</b>                     | $\infty$                                 |
| <b>2</b>                     | $\infty$                                 |
| <b>3</b>                     | $\infty$                                 |
| <b>4</b>                     | $\infty$                                 |
| <b>5</b>                     | <b>~15</b>                               |
| <b>6</b>                     | <b>~2</b>                                |

**Table S2.** Resistance of graphene thin film on glass with different spin-coating times.

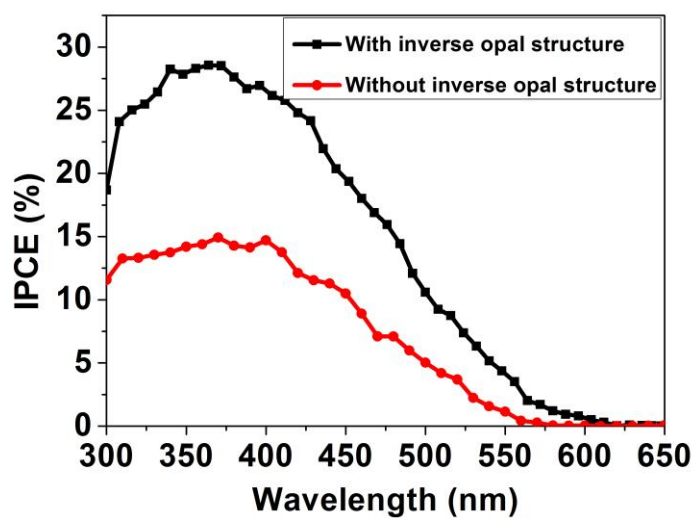


**Figure S6.** AFM image of graphene thin film with spin coating of 5 times.

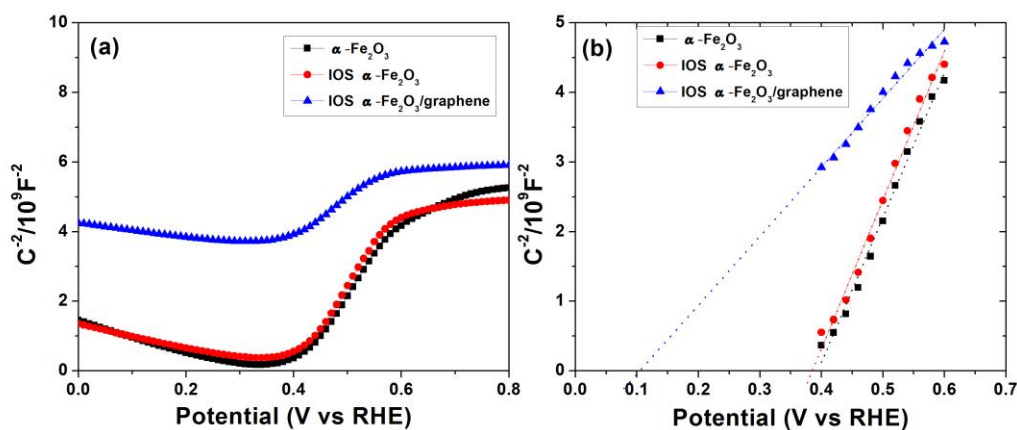




**Figure S7.** FE-SEM images of  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub> film without any structure prepared by electrodeposition method.

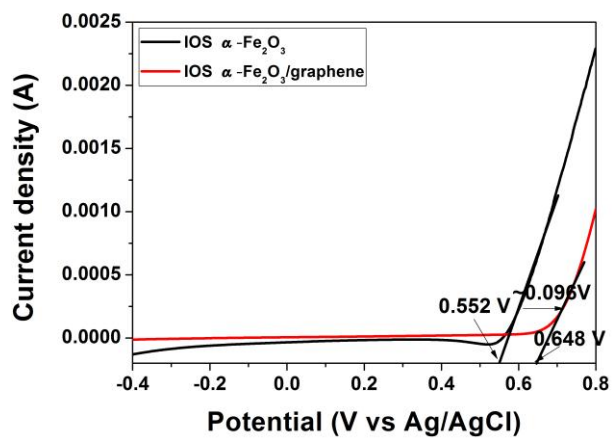


**Figure S8.** IPCE results of inverse opal structure and general structure  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub> at 0.5 V vs Ag/AgCl under illumination by AM 1.5G light in 1 M NaOH electrolyte.



**Figure S9.** Mott-Schottky plots of  $\alpha\text{-Fe}_2\text{O}_3$ , IOS  $\alpha\text{-Fe}_2\text{O}_3$  and IOS  $\alpha\text{-Fe}_2\text{O}_3/\text{graphene}$ -5 electrodes in 0.5 M NaOH electrolyte.

Reversed sigmoidal plots were observed with an overall shape relevant to typical for n-type  $\alpha\text{-Fe}_2\text{O}_3$  (Figure S7a). The flat-band voltage ( $V_{fb}$ ), which was calculated to be 0.41, 0.39 and 0.09 V vs RHE in 0.5 M NaOH electrolyte (equivalent to 0.61, 0.59 and 0.29 V vs. NHE) from the x intercepts of the linear region corresponding to  $\alpha\text{-Fe}_2\text{O}_3$ , IOS  $\alpha\text{-Fe}_2\text{O}_3$  and IOS  $\alpha\text{-Fe}_2\text{O}_3/\text{graphene}$ -5 (Figure S7b). It is well-known that  $V_{fb}$  equals the Fermi Level ( $E_F$ ) for n-type semiconductors, and is an inherent property of such semiconductors[4]. In addition, the calculated  $E_F$  of graphene is  $-0.08$  eV vs NHE [5,6], which is more negative than the Fermi level of  $\alpha\text{-Fe}_2\text{O}_3$ , resulting in hinder electron transfer from  $\alpha\text{-Fe}_2\text{O}_3$  to graphene. However, the accumulation of electrons inevitably causes shifting of the apparent Fermi level ( $E_F^*$ ) [7, 8], so that the  $V_{fb}$  of IOS  $\alpha\text{-Fe}_2\text{O}_3/\text{graphene}$ -5 shifts negatively compared to that of IOS  $\alpha\text{-Fe}_2\text{O}_3$ . On the other band, the  $E_F$  of FTO is negative enough to accept electrons from  $\alpha\text{-Fe}_2\text{O}_3$  excited. Thus, the electronic interaction between graphene/FTO substrate and IOS  $\alpha\text{-Fe}_2\text{O}_3$  may cause a cathodic shift of the  $E_F^*$ , resulting in a higher conduction band position which allows charge transfer from  $\alpha\text{-Fe}_2\text{O}_3$  to graphene.



**Figure S10.** Dark current of IOS  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub> and IOS  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>/graphene-5 electrodes in 0.5 M NaOH electrolyte.

## Reference

- [S1] Yang, D.; Velamakanni, A.; Bozoklu, G.; Park, S.; Stoller, M.; Piner, R.; Stankovich, S.; Jung, I.; Field, D., Jr.; Ruoff, R.; Chemical analysis of graphene oxide films after heat and chemical treatments by X-ray photoelectron and Micro-Raman spectroscopy. *Carbon* 2009, 47, 145–152
- [S2] Zhang, W.; Cui, J.; Tao, C.; Wu, Y.; Li, Z.; Ma, L.; Wen, Y.; Li, G.; Strategy for Producing Pure Single-Layer Graphene Sheets Based on a Confined Self-Assembly Approach. *Angewandte Chemie International Edition* 2009, 48, 5864–5868.
- [S3] Lu, J.; Yang, J.; Wang, J.; Lim, A.; Wang, S.; Loh, K.; One-Pot Synthesis of Fluorescent Carbon Nanoribbons, Nanoparticles, and Graphene by the Exfoliation of Graphite in Ionic Liquids. *ACS Nano*. 2009, 3, 2367–2375.
- [S4] Scaife, D.; Oxide semiconductors in photoelectrochemical conversion of solar energy. *Solar Energy* 1980, 25, 41–54.
- [S5] Wang, X.; Zhi, L.; Mullen, K.; Transparent, Conductive Graphene Electrodes for Dye-Sensitized Solar Cells. *Nano Letters* 2008, 8, 323–327
- [S6] Khomyakov, P.; Giovannetti, G.; Rusu, P.; Brocks, G.; van den Brink, J.; Kelly, P.; First-principles study of the interaction and charge transfer between graphene and metals. *Physical Review B* 2009, 79, 195425–195436.
- [S7] Subramanian, V.; Wolf, E.; Kamat, P.; Catalysis with TiO<sub>2</sub>/Gold Nanocomposites. Effect of Metal Particle Size on the Fermi Level Equilibration. *Journal of the American Chemical Society* 2004, 126, 4943–4950.
- [S8] Kongkanand, A.; Kamat, P.; Electron Storage in Single Wall Carbon Nanotubes. Fermi Level Equilibration in Semiconductor–SWCNT Suspensions. *ACS Nano* 2007, 1, 13–21.